

**3rd International Conference on
Modulated Semiconductor
Structures**

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**3rd International Conference on
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PREFACE

This volume contains papers presented at the Third International Conference on Modulated Semiconductor Structures, which was held at the Université des Sciences et Techniques du Languedoc, Montpellier, France, on 6-10 July 1987. The papers were reviewed, and revised when necessary : we wish to thank the referees and the authors for their involvement in completing this volume in a relatively short time.

The conference was organized by a committee consisting of G. Bastard, C. Bousquet, J.M. Dusseau, A. Raymond, J.L. Robert, J. Sicart, P. Voisin and M. Voos, with the help of a program committee and the advice of an international advisory committee. The members of these committees are listed on the previous page.

As the earlier conferences held in Pasadena, December 1982 (Journal of Vacuum Science and Technology Vol. B1(2)) and in Kyoto, September 1985 (Surface Science Vol. 174), MSS III aimed at providing a forum for the communication and discussion of updated information in the fast moving field of epitaxial growth, characterization of the structural and electronic properties, and applications of semiconductor heterostructures. The conference was attended by 255 physicists from 18 countries, representing most of the research groups active in the field. Fourteen invited papers and 130 contributed papers (including both oral and poster presentations) were presented. These contributions demonstrated both the sustained interest in the traditional scopes of the conference such as growth, characterization and optical properties of a variety of systems (including the newly grown heterostructures of semimagnetic II-VI compounds), and the rapid development of relatively new fields like sub-picosecond time resolved investigations and sophisticated tunneling heterostructures.

Finally, on behalf of the participants, we wish to thank all the sponsors of MSS III for their essential financial support to the conference.

August 1987
A. Raymond
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